CLAIMS

1. An integrated assembly, comprising:

a conductive expanse over conductive nodes; the conductive nodes comprising a first composition; a bottom surface of the conductive expanse comprising a second composition different from the first composition, the bottom surface of the conductive expanse being at an elevation above a base that is greater than or equal to an elevation above the base of an uppermost surface the conductive nodes;

a stack over the conductive expanse; the stack comprising alternating first and second levels; the stack including a memory array region, a staircase region adjacent the memory array region, and a peripheral region adjacent the memory array region; a first set of the conductive nodes being under the memory array region; and

pillar structures extending vertically through the stack; each of the pillar structures comprising a post of conductive material laterally surrounded by an insulative liner, the insulative liner being in direct physical contact with the post of conductive material along an entirety of the post above the conductive expanse and not extending below the bottom surface of the conductive expanse; a first set of the pillar structures extending through the memory array region, a second set of the pillar structures extending through the peripheral region, and a third set of the pillar structures extending through the staircase region; the posts of the first set of the pillar structures extending through the conductive expanse to directly contact the first set of the conductive nodes.

2. The integrated assembly of claim 1 wherein the first levels comprise conductive wordline material and the second levels

are insulative levels.

3. The integrated assembly of claim 1 further comprising a second set of the conductive nodes under the peripheral region; and wherein the posts of the second set of the pillar structures extend through the conductive expanse to directly contact the second set of the conductive nodes.

4. The integrated assembly of claim 3 further comprising a third set of the conductive nodes under the staircase region; and wherein the posts of the third set of the pillar structures extend through the conductive expanse to directly contact the third set of the conductive nodes.

5. The integrated assembly of claim 1 wherein the memory array region is a NAND memory array region.

6. The integrated assembly of claim 1 wherein the conductive material of the posts comprises the first composition.

7. The integrated assembly of claim 1 further comprising a first set of collars surrounding regions of the posts of the first set of the pillar structures; said regions being immediately below the bottom surface of the conductive expanse.

8. The integrated assembly of claim 7 comprising a second set of the conductive nodes under the peripheral region; the posts of the second set of the pillar structures extending through the conductive expanse to directly contact the second set of the conductive nodes; a second set of the collars surrounding regions of the posts of the second set of the pillar structures; said regions of the posts of the second set of the pillar structures being

immediately below the bottom surface of the conductive expanse.

9. The integrated assembly of claim 8 wherein the conductive expanse comprises second region over a first region, with the first region comprising the second composition and the second region comprising a third composition; wherein a third set of conductive nodes is within the second region; and wherein the posts of the third set of the pillar structures terminate at the conductive nodes of the third set.

10. The integrated assembly of claim 9 wherein:

the second composition comprises tungsten silicide;

the third composition comprises conductively-doped silicon; and

the conductive nodes of the third set comprise tungsten.

11. The integrated assembly of claim 8 comprising a third set of the conductive nodes under the staircase region; the posts of the third set of the pillar structures extending through the conductive expanse to directly contact the third set of the conductive nodes; a third set of the collars surrounding regions of the posts of the third set of the pillar structures; said regions of the posts of the third set of the pillar structures being immediately below the bottom surface of the conductive expanse.